

Figure 1 consists of four cross-sectional views (a, b, c, d) of a semiconductor device, showing the progression of a manufacturing process. The device is built on a substrate 200, which has a layer 201 and a layer 202. A patterned layer 203a is formed on top of 202. In view (a), a layer 204a is formed on 203a, and a layer 206 is formed on 204a. In view (b), a layer 214a is formed on 206, and a layer 206a is formed on 214a. In view (c), a layer 215 is formed on 206a, and a layer 214a is formed on 215. In view (d), a layer 214b is formed on 214a, and a layer 206a is formed on 214b. The layers are labeled with reference numerals: 200, 201, 202, 203a, 204a, 205, 206, 206a, 214, 214a, 214b, and 215.